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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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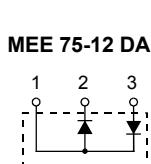
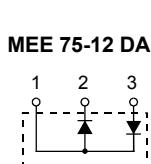
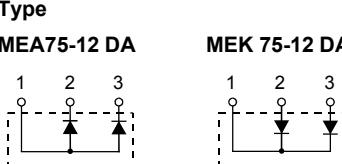
Fast Recovery Epitaxial Diode (FRED) Module

MEA 75-12 DA
MEK 75-12 DA
MEE 75-12 DA

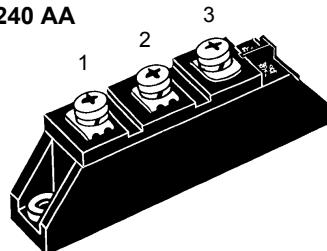
V_{RRM} = 1200 V
I_{FAV} = 75 A
t_{rr} = 250 ns

Preliminary data

V _{RSM} V	V _{RRM} V	Type	MEA75-12 DA	MEK 75-12 DA	MEE 75-12 DA
1200	1200		1 2 3	1 2 3	1 2 3



TO-240 AA



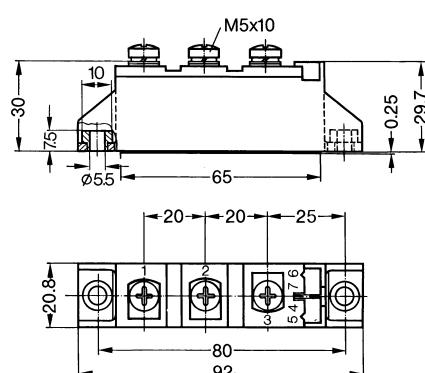
Symbol	Test Conditions	Maximum Ratings		
I _{FRMS}	T _{case} = 75 °C	107	A	
I _{FAV}	T _{case} = 75 °C; rectangular, d = 0.5	75	A	
I _{FRM}	t _p < 10 µs; rep. rating, pulse width limited by T _{VJM}	TBD	A	
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	1200	A	
	t = 8.3 ms (60 Hz), sine	1300	A	
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	1080	A	
	t = 8.3 ms (60 Hz), sine	1170	A	
I ² t	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	7200	A ² s	
	t = 8.3 ms (60 Hz), sine	7100	A ² s	
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	5800	A ² s	
	t = 8.3 ms (60 Hz), sine	5700	A ² s	
T _{VJ}		-40...+150	°C	
T _{stg}		-40...+125	°C	
T _{Hmax}		110	°C	
P _{tot}	T _{case} = 25°C	280	W	
V _{ISOL}	50/60 Hz, RMS t = 1 min	3000	V _~	
	I _{ISOL} ≤ 1 mA t = 1 s	3600	V _~	
M _d	Mounting torque (M5)	2.50-4/22-35	Nm/lb.in.	
	Terminal connection torque (M5)	2.50-4/22-35	Nm/lb.in.	
d _S	Creep distance on surface	12.7	mm	
d _A	Strike distance through air	9.6	mm	
a	Maximum allowable acceleration	50	m/s ²	
Weight		90	g	

Symbol	Test Conditions	Characteristic Values (per diode)	
		typ.	max.
I _R	T _{VJ} = 25°C V _R = V _{RRM}	2	mA
	T _{VJ} = 25°C V _R = 0.8 • V _{RRM}	0.5	mA
	T _{VJ} = 125°C V _R = 0.8 • V _{RRM}	34	mA
V _F	I _F = 100 A; T _{VJ} = 125°C	1.85	V
	T _{VJ} = 25°C	2.17	V
	I _F = 300 A; T _{VJ} = 125°C	2.58	V
	T _{VJ} = 25°C	2.64	V
V _{T0}	For power-loss calculations only	1.48	V
r _T		3.65	mΩ
R _{thJH}	DC current	0.550	K/W
R _{thJC}	DC current	0.450	K/W
t _{rr}	I _F = 150 A T _{VJ} = 100°C	250	ns
I _{RM}	V _R = 600 V T _{VJ} = 25°C	300	ns
	-di/dt = 200 A/µs T _{VJ} = 100°C	22	A
		33	A

Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

Dimensions in mm (1 mm = 0.0394")



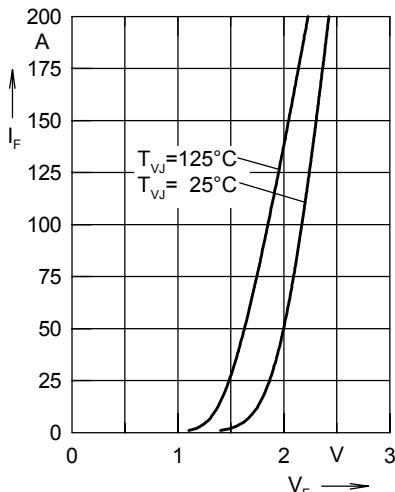


Fig. 1 Forward current I_F versus voltage drop V_F per leg

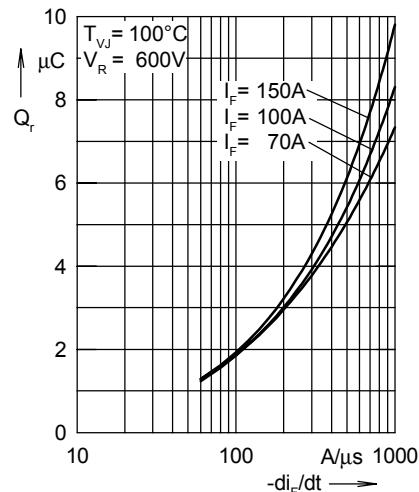


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

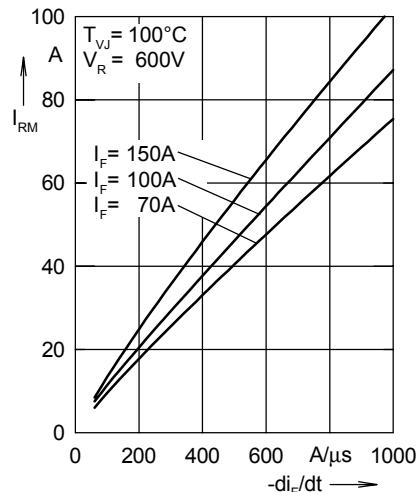


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

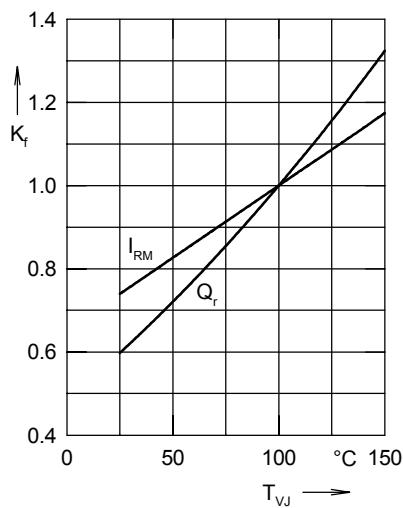


Fig. 4 Dynamic parameters Q_r , I_{RM} versus junction temperature T_{VJ}

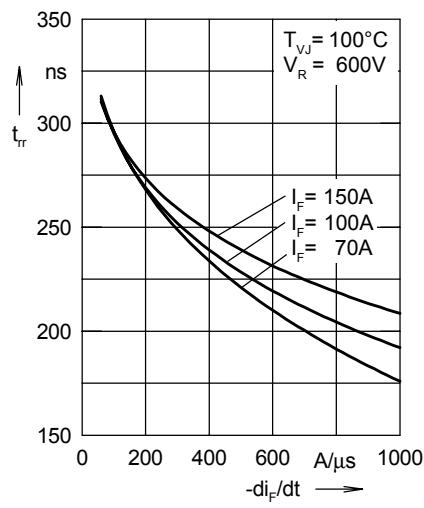


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

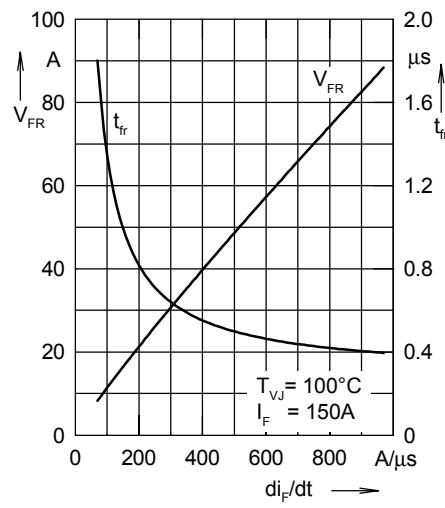


Fig. 6 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt

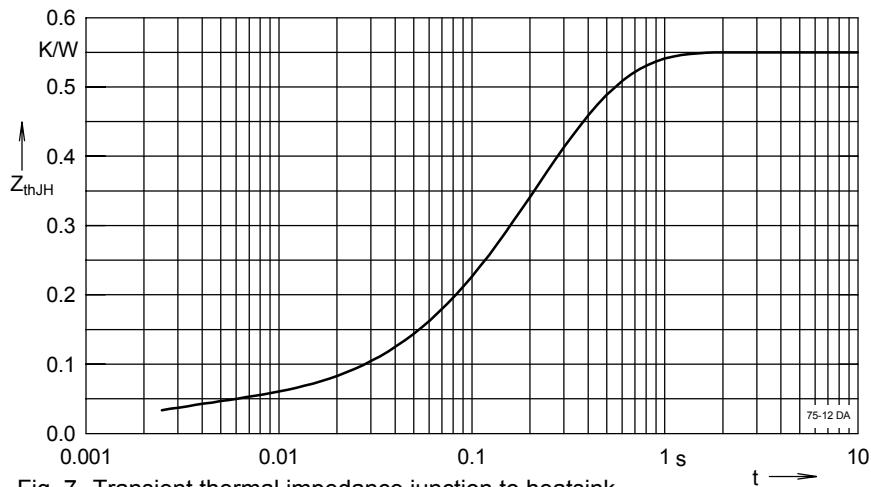


Fig. 7 Transient thermal impedance junction to heatsink

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.037	0.002
2	0.138	0.134
3	0.093	0.25
4	0.282	0.274